

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently amended) A method for polishing a semiconductor wafer, in which the semiconductor wafer is polished by continuously driving a surface plate on which a plurality of polishing pads are stuck, the surface of each of the polishing pads being provided with a plurality of grooves each extending linearly in the drive direction of the pad,

the method comprising the steps of:

sticking the plurality of polishing pads on the surface of the surface plate; and

polishing the semiconductor wafer by pressing the wafer against the surface of each said polishing pad with the surface plate driven,

wherein in the sticking step, the polishing pads are stuck in such a manner that the grooves of each said polishing pad are spaced not to align with the respective grooves of the polishing pad adjacently arranged in the drive direction of the surface plate.

2. (Original) The method of claim 1, wherein in the sticking step, the polishing pads are stuck in such a manner that the grooves of each said polishing pad are offset by a predetermined distance from the respective grooves of the polishing pad adjacently arranged in the drive direction.

3. (Original) The method of claim 1, wherein in the polishing step, the semiconductor wafer is polished with slurry containing abrasives flowing on the surfaces of the polishing pads.

4. (Currently amended) A polishing pad for a semiconductor wafer, wherein the polishing pad is stuck on the surface of a belt-type surface plate, and

a plurality of grooves extending linearly in the drive direction of the polishing pad are formed over the entire width from edge to edge of the polishing pad in the direction perpendicular to the drive direction.

5. (Original) The pad of claim 4, wherein the plurality of grooves are formed at regular intervals.

6. (Original) The pad of claim 4, wherein the polishing pad is made of polyurethane foam.

7-9. (Cancelled)